

32000 U.S. PTO
09/904129

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Class	Subclass	ISSUE CLASSIFICATION
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PATENT NUMBER

U.S. UTILITY Patent Application

O.I.P.E. SCANNED <i>AK</i> <i>TKI</i> <i>Q.A.</i> <i>EW</i>	PATENT DATE
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APPLICATION NO. 09/904129	CONT/PRIOR	CLASS 428 117	SUBCLASS 698 84	ART UNIT 4775 1765	EXAMINER STEIN
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APPLICANTS

Tetsuzo Ueda

SONG

Buffer layer and growth method for subsequent epitaxial growth of
InAlV nitride semiconductors

PTO-2040
12/89

ISSUING CLASSIFICATION

ORIGINAL		CROSS REFERENCE(S)			
CLASS	SUBCLASS	CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)		
INTERNATIONAL CLASSIFICATION					

☐ Continued on Issue Slip Inside File Jacket

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	_____ (Assistant Examiner) _____ (Date)			NOTICE OF ALLOWANCE MAILED ISSUE FEE Amount Due Date Paid	
	_____ (Primary Examiner) _____ (Date)			ISSUE BATCH NUMBER _____ (Legal Instruments Examiner) _____ (Date)	

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